

SEMICONDUCTOR TECHNICAL DATA

KTD2059

TRIPLE DIFFUSED NPN TRANSISTOR

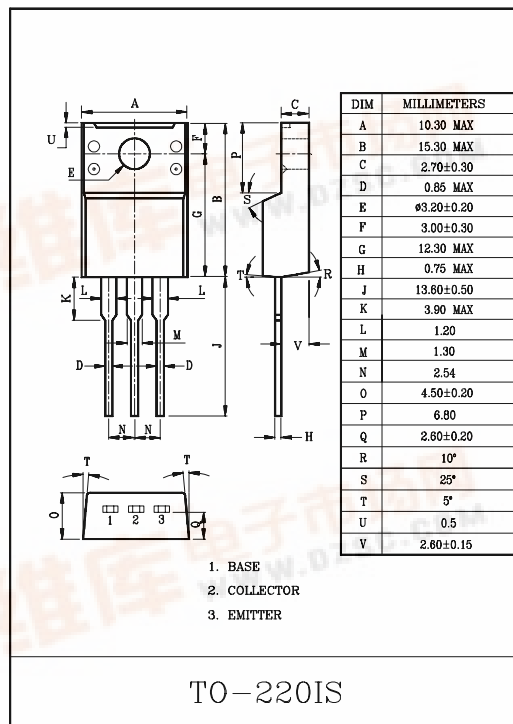
GENERAL PURPOSE APPLICATION.

FEATURE

- Complementary to KTB1367.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	5	A
Base Current	I_B	0.5	A
Collector Power Dissipation (Tc=25°C)	P_C	30	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=100V, I_E=0$	-	-	100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	1.0	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=50mA, I_B=0$	100	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=5V, I_C=1A$	40	-	240	
	$h_{FE(2)}$	$V_{CE}=5V, I_C=4A$	20	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=4A, I_B=0.4A$	-	-	2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=5V, I_C=1A$	-	-	1.5	V
Transition Frequency	f_T	$V_{CE}=5V, I_C=1A$	-	12	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	100	-	pF

Note : $h_{FE(1)}$ Classification R:40~80, O:70~140, Y:120~240

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